

ON Semiconductor®

# FDC6302P Digital FET, Dual P-Channel

### **General Description**

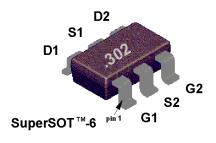
These Dual P-Channel logic level enhancement mode field effect transistors are produced using ON Semiconductor's proprietary, high cell density, DMOS technology. This very high density process is especially tailored to minimize onstate resistance. This device has been designed especially for low voltage applications as a replacement for digital transistors in load switching applications. Since bias resistors are not required this one P-Channel FET can replace several digital transistors with different bias resistors like the IMBxA series.

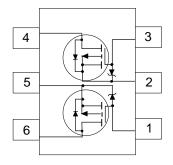
#### Features

( level gate drive requirements allowing dis-

- Very low level gate drive requirements allowing direct operation in 3V circuits. V<sub>GS(th)</sub> < 1.5V.</li>
- Gate-Source Zener for ESD ruggedness.>6kV Human Body Model
- Replace multiple PNP digital transistors (IMHxA series) with one DMOS FET.







## **Absolute Maximum Ratings** $T_A = 25^{\circ}C$ unless other wise noted

| Symbol           | Parameter  |           | FDC6302P   | Units    |
|------------------|--|-----------|------------|----------|
| V <sub>DSS</sub> | Drain-Source Voltage   |           | -25        | V        |
| $V_{GSS}$        | Gate-Source Voltage  |           | -8         | V        |
| I <sub>D</sub>   | Drain Current - Continuous   |           | -0.12      | А        |
|                  | - Pulsed   |           | -0.5       |          |
| P <sub>D</sub>   | Maximum Power Dissipation  | (Note 1a) | 0.9        | W        |
|                  |  | (Note 1b) | 0.7        |          |
| $T_{J},T_{STG}$  | Operating and Storage Temperature Range  |           | -55 to 150 | °C       |
| ESD              | Electrostatic Discharge Rating MIL-STD-883I<br>Human Body Model (100pf / 1500 Ohm) | )         | 6.0        | kV       |
| THERMA           | L CHARACTERISTICS  | •         |            | <u>.</u> |
| R <sub>eja</sub> | Thermal Resistance, Junction-to-Ambient  | (Note 1a) | 140        | °C/W     |
| R <sub>euc</sub> | Thermal Resistance, Junction-to-Case   | (Note 1)  | 60         | °C/W     |

| Symbol                           | Parameter                                 | Conditions   | Min   | Тур   | Max  | Units  |
|----------------------------------|---|--|-------|-------|------|--------|
| OFF CHAR                         | ACTERISTICS                               |  | •     |       |      |        |
| BV <sub>DSS</sub>                | Drain-Source Breakdown Voltage            | $V_{GS} = 0 \text{ V}, I_{D} = -250 \mu\text{A}$                           |       |       |      | V      |
| $\Delta BV_{DSS}/\Delta T_{J}$   | Breakdown Voltage Temp. Coefficient       | I <sub>D</sub> = -250 μA, Referenced to 25 °C                              |       | -20   |      | mV /°C |
| I <sub>DSS</sub>                 | Zero Gate Voltage Drain Current           | $V_{DS} = -20 \text{ V}, \ V_{GS} = 0 \text{ V}$                           |       |       | -1   | μA     |
|                                  |   | $T_{_{\rm J}} = 55^{\circ}\text{C}$  |       |       | -10  | μΑ     |
| I <sub>GSS</sub>                 | Gate - Body Leakage Current               | V <sub>GS</sub> = -8 V, V <sub>DS</sub> = 0 V                              |       |       | -100 | nA     |
| ON CHARA                         | CTERISTICS (Note 2)                       |  |       |       |      |        |
| $\Delta V_{GS(th)}/\Delta T_{J}$ | Gate Threshold Voltage Temp. Coefficient  | I <sub>D</sub> = -250 μA, Referenced to 25 °C                              |       | 1.9   |      | mV /°C |
| V <sub>GS(th)</sub>              | Gate Threshold Voltage                    | $V_{DS} = V_{GS}, \ I_{D} = -250 \ \mu A$                                  | -0.65 | -1    | -1.5 | V      |
| R <sub>DS(ON)</sub>              | Static Drain-Source On-Resistance         | $V_{GS} = -2.7 \text{ V}, I_{D} = -0.05 \text{A}$                          |       | 10.6  | 13   | Ω      |
| -(- /                            |   | $V_{GS} = -4.5 \text{ V}, I_{D} = -0.2 \text{ A}$                          |       | 7.9   | 10   |        |
|                                  |   | T <sub>J</sub> =125°C  |       | 12    | 18   |        |
| I <sub>D(ON)</sub>               | On-State Drain Current                    | $V_{GS} = -2.7 \text{ V}, \ V_{DS} = -5 \text{ V}$                         | -0.05 |       |      | Α      |
| g <sub>FS</sub>                  | Forward Transconductance                  | $V_{DS} = -5 \text{ V}, \ I_{D} = -0.2 \text{ A}$                          |       | 0.135 |      | S      |
| DYNAMIC C                        | HARACTERISTICS                            |  |       |       | •    |        |
| C <sub>iss</sub>                 | Input Capacitance                         | $V_{DS} = -10 \text{ V}, V_{GS} = 0 \text{ V},$<br>f = 1.0 MHz             |       | 11    |      | pF     |
| C <sub>oss</sub>                 | Output Capacitance                        |  |       | 7     |      | pF     |
| C <sub>rss</sub>                 | Reverse Transfer Capacitance              |  |       | 1.4   |      | pF     |
| SWITCHING                        | CHARACTERISTICS (Note 2)                  |  |       |       |      |        |
| t <sub>D(on)</sub>               | Turn - On Delay Time                      | $V_{DD} = -6 \text{ V}, \ I_{D} = -0.2 \text{ A},$                         |       | 5     | 12   | ns     |
| t <sub>r</sub>                   | Turn - On Rise Time                       | $V_{GS} = -4.5 \text{ V}, R_{GEN} = 50 \Omega$                             |       | 8     | 16   | ns     |
| $\mathbf{t}_{D(off)}$            | Turn - Off Delay Time                     |  |       | 9     | 18   | ns     |
| t <sub>f</sub>                   | Turn - Off Fall Time                      |  |       | 5     | 10   | ns     |
| $Q_g$                            | Total Gate Charge                         | $V_{DS} = -5 \text{ V}, I_{D} = -0.2 \text{ A},$ $V_{GS} = -4.5 \text{ V}$ |       | 0.22  | 0.31 | nC     |
| $Q_{gs}$                         | Gate-Source Charge                        |  |       | 0.12  |      | nC     |
| $Q_{gd}$                         | Gate-Drain Charge                         |  |       | 0.05  |      | nC     |
| DRAIN-SOU                        | RCE DIODE CHARACTERISTICS AND MAX         | IMUM RATINGS   | 1     |       | ı    | 1      |
| l <sub>s</sub>                   | Maximum Continuous Drain-Source Diode For | orward Current   |       |       | -0.7 | Α      |
| V <sub>SD</sub>                  | Drain-Source Diode Forward Voltage        | $V_{GS} = 0 \text{ V}, I_{S} = -0.7 \text{ A} \text{ (Note 2)}$            |       | -1    | -1.3 | V      |

Notes:

1. R<sub>Bux</sub> is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. R<sub>Buc</sub> is guaranteed by design while R<sub>Buc</sub> is determined by the user's board design.



a. 140°C/W on a 0.125 in² pad of 2oz copper.



b. 180°C/W on a 0.005 in² of pad of 2oz copper.

2. Pulse Test: Pulse Width  $\leq$  300 $\mu$ s, Duty Cycle  $\leq$  2.0%.

# **Typical Electrical Characteristics**

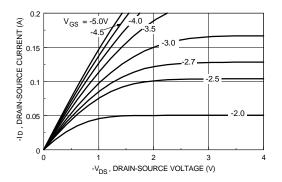


Figure 1. On-Region Characteristics.

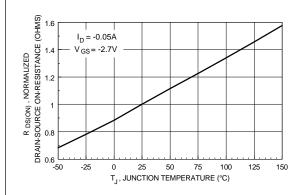


Figure 3. On-Resistance Variation with Temperature.

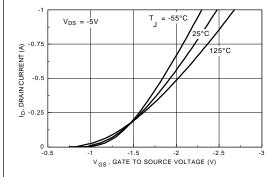


Figure 5. Transfer Characteristics.

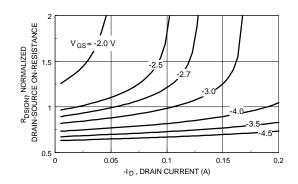


Figure 2. On-Resistance Variation with Drain Current and Gate Voltage.

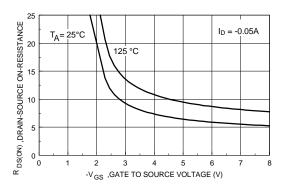


Figure 4. On Resistance Variation with Gate-To- Source Voltage.

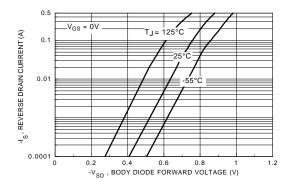


Figure 6. Body Diode Forward Voltage Variation with Source Current and Temperature.

# **Typical Electrical And Thermal Characteristics**

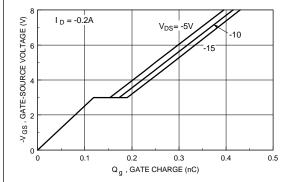


Figure 7. Gate Charge Characteristics.

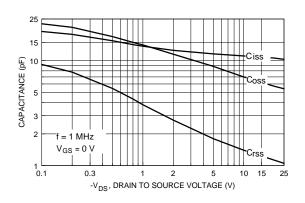


Figure 8. Capacitance Characteristics.

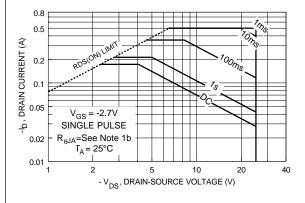


Figure 9. Maximum Safe Operating Area.

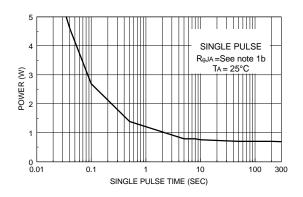


Figure 10. Single Pulse Maximum Power Dissipation.

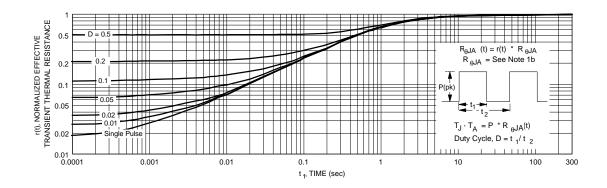


Figure 11. Transient Thermal Response Curve.

Note: Thermal characterization performed using the conditions described in note 1b.Transient thermal response will change depending on the circuit board design.

ON Semiconductor and in are trademarks of Semiconductor Components Industries, LLC dba ON Semiconductor or its subsidiaries in the United States and/or other countries. ON Semiconductor owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of ON Semiconductor's product/patent coverage may be accessed at <a href="www.onsemi.com/site/pdf/Patent-Marking.pdf">www.onsemi.com/site/pdf/Patent-Marking.pdf</a>. ON Semiconductor reserves the right to make changes without further notice to any products herein. ON Semiconductor makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does ON Semiconductor assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. Buyer is responsible for its products and applications using ON Semiconductor products, including compliance with all laws, regulations and safety requirements or standards, regardless of any support or applications information provided by ON Semiconductor. "Typical" parameters which may be provided in ON Semiconductor data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. ON Semiconductor does not convey any license under its patent rights nor the rights of others. ON Semiconductor products are not designed, intended, or authorized for use as a critical component in life support systems or any FDA Class 3 medical devices or medical devices with a same or similar classification in a foreign jurisdiction or any devices intended for implantation in the human body. Should Buyer purchase or use ON Semiconductor products for any such unintended or unauthorized application, Buyer shall indemnify and hol

### **PUBLICATION ORDERING INFORMATION**

#### LITERATURE FULFILLMENT:

Literature Distribution Center for ON Semiconductor 19521 E. 32nd Pkwy, Aurora, Colorado 80011 USA Phone: 303-675-2175 or 800-344-3860 Toll Free USA/Canada Fax: 303-675-2176 or 800-344-3867 Toll Free USA/Canada Email: orderlit@onsemi.com N. American Technical Support: 800-282-9855 Toll Free USA/Canada Europe, Middle East and Africa Technical Support: Phone: 421 33 790 2910

Phone: 421 33 790 2910

Japan Customer Focus Center
Phone: 81–3–5817–1050

ON Semiconductor Website: www.onsemi.com

Order Literature: http://www.onsemi.com/orderlit

For additional information, please contact your local Sales Representative

# **Mouser Electronics**

**Authorized Distributor** 

Click to View Pricing, Inventory, Delivery & Lifecycle Information:

**ON Semiconductor:** 

FDC6302P